insulative material to prevent short circuiting between the first conductive material and the second conductive material and to provide electrical insulation between the first and second conductive materials and the semiconductor substrate.

27. (Amended) The method of claim 18, further comprising between depositing a first conductive material and forming at least one second trench, depositing [an] the insulative material within each first trench over the first conductive material.

29. (Amended) The method of claim 18, further comprising after depositing a second conductive material, depositing [an] a further insulative material within each second trench over the second conductive material.

30. (Amended) The method of claim 29, wherein the further insulative material comprises silicon dioxide.

31. (Amended) The method of claim 18, further comprising between forming at least one first trench and depositing a first conductive material, forming [an] the insulating layer at the bottom of and on walls of each first trench.

33. (Amended) The method of claim 18, further comprising between forming at least one second trench and depositing a second conductive material, forming [an] a second insulating layer at the bottom of and on walls of each second trench.

34. (Amended) The method of claim 33, wherein forming the second insulating layer comprises oxidizing the bottom of and the walls of each second trench.

39. (Amended) A method comprising:

burying first conductive elements within a semiconductor substrate at a first depth;

burying second conductive elements within a semiconductor substrate at a second depth

less than the first depth; and

surrounding the first conductive elements and the second conductive elements to prevent short circuiting and to electrically insulate the first and second conductive elements from the semiconductor substrate.

42. (Amended) A method, comprising:

forming communication layers in a substrate;

forming an active semiconductor layer above the communication layers on the substrate; and

wherein forming the communication layers includes:

forming at least one first trench within a semiconductor substrate at a first depth;

forming [an] a first insulating layer at a bottom and sidewalls of the at least one first trench;

depositing a first seed material to facilitate deposition of a first conductive material in the at least one first trench;

depositing the first conductive material substantially at the bottom of each first trench;

forming at least one second trench within the semiconductor substrate at a second depth shallower than the first depth;

forming [an] a second insulating layer at a bottom and sidewalls of the at least one second trench;

depositing a second seed material to facilitate deposition of a second conductive material in the at least one second trench;

depositing the second conductive material substantially at the bottom of each second trench; [and]

forming a [first] third insulating layer on the first conductive material to prevent short circuiting to the second conductive material; and

electrically insulating the first conductive layer from the semiconductor substrate.

43. (Amended) The method of claim 42, wherein depositing the second conductive material includes forming a [second] fourth insulating layer on the second conductive material.

44. (Amended) The method of claim 43, wherein forming the active semiconductor layer includes forming the active semiconductor layer on the [second] fourth insulating layer.

45. (Amended) The method of claim 44, wherein forming the active semiconductor layer includes forming a P-type epitaxial layer on the [second] fourth insulating layer.

47. (Amended) The method of claim 46, wherein forming the active circuitry includes forming a trench capacitor that extends between the second conductive material in two of the at least [two] one second trenches.